IN THE CLAIMS:

Claim 1 (Previously presented): An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, provided with a T-shaped gate electrode comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode and having a length larger than the width of source and drain regions, and having a thickness of a gate insulating film formed directly under the entire region of the crosspiece-shaped conductor pattern greater than the thickness of the gate insulating film directly under the main gate electrode.

Claim 2 (Currently amended): An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a thickness of ~~an~~ a first insulating film provided on a surface of a first conductivity type semiconductor region positioned at an interface between a first conductivity type body contact region, for draining carriers stored at a channel region under a gate, and a second conductivity type source and drain regions is made greater than the thickness of a ~~gate~~ second insulating film, acting as a gate insulating film, with a uniform thickness directly under a gate electrode, said gate electrode being provided on the region except for said body contact region.

Claim 3 (Currently amended): An insulated gate type semiconductor device ~~comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein~~ as set forth in claim 2, said first insulating film is formed as a buried insulating film ~~thicker than the thickness of a gate insulating film with a uniform thickness directly under a gate electrode is provided on a surface of a first conductivity type semiconductor region positioned at an interface between a first conductivity type body contact region and a second conductivity type source and drain regions, said gate electrode being provided on the region except for said body contact region~~.

Claim 4 (canceled)

Claim 5 (previously presented): An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a gate electrode of a shape of either one of an L-shape or asymmetric T-shape comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode is provided and, said trunk-shaped main gate electrode is sandwiched between a source region and a drain region, and at least part of said cross-piece-shaped conductor pattern is also sandwiched between said source region and said drain region, and thereby at least part of said crosspiece-shaped conductor pattern functions as an effective gate electrode.

Claims 6 (withdrawn): A method for fabricating an insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, comprising the steps of:

providing a gate insulating film partially differing in thickness on the surface of said semiconductor layer;

providing a crosspiece-shaped conductor pattern on a thick portion of said gate insulating film and providing a trunk-shaped main gate electrode on the gate insulating film to form a T-shaped gate electrode;

forming sidewalls on side faces of said gate electrode;

doping an impurity using said main gate electrode and crosspiece-shaped conductor pattern as a mask to form source and drain regions;

doping an impurity using said crosspiece-shaped conductor pattern as a mask to form a body contact region; and

depositing a metal film over the entire surface and then performing heat treatment to form a silicide electrode.

Claims 7 (withdrawn): A method for fabricating an insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, comprising the steps of:

providing a gate insulating film partially differing in thickness on the surface of said

semiconductor layer;

providing a crosspiece-shaped conductor pattern on a thick portion of said gate insulating film and providing a trunk-shaped main gate electrode on the gate insulating film to form a T-shaped gate electrode;

forming sidewalls on side faces of said gate electrode;

doping an impurity using said main gate electrode and crosspiece-shaped conductor pattern as a mask to form source and drain regions;

doping an impurity using said crosspiece-shaped conductor pattern as a mask to form a body contact region; and

removing said crosspiece-shaped conductor pattern, then depositing a metal film over the entire surface and performing heat treatment to form a silicide electrode.

Claims 8 (withdrawn): A method for fabricating an insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, comprising the steps of:

forming a groove of a different depth in the surface of said semiconductor layer and burying the groove by an insulator to form an element isolation insulating film and an intra-element isolation insulating film;

providing a gate electrode on a gate insulating film;

forming sidewalls on side faces of said gate electrode;

doping an impurity using said gate electrode and said intra-element isolation insulating

film as a mask to form source and drain regions;

doping an impurity using said intra-element isolation insulating film as a mask to form a body contact region; and

depositing a metal film over the entire surface and then performing heat treatment to form a silicide electrode.

Claim 9 (previously presented): An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a gate electrode of a shape of an asymmetric T-shape comprised of a trunk-shaped main gate electrode and a crosspiece-shaped conductor pattern is provided and a body contact region and one of a source region and drain region are isolated through said crosspiece-shaped conductor pattern, said body contact region being made the same potential as one of said source region and drain region.